



Transys
Electronics
LIMITED

B0530W SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D : 410 mW (Tamb=25°C)

Collector current

I_F : 5.5 A

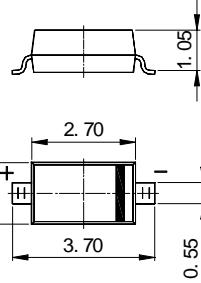
Collector-base voltage

V_R : 30 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

SOD-123



Unit: mm

MARKING: SE

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 200$	30		V
Reverse voltage leakage current	I_R	$V_R = 15V$ $V_R = 30V$		20 130	μA
Forward voltage	V_F	$I_F = 0.1A$ $I_F = 0.5A$		0.375 0.43	V
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		170	pF